

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PATENT

IN RE APPLICATION OF: HWANG ET AL.

SERIAL NO.: 10/022,349

GROUP ART UNIT: 2814

FILED: December 20, 2001

EXAMINER: D. WILLIE

FOR: A SINGLE-CHIP STRUCTURE OF SILICON
GERMANIUM PHOTODETECTOR AND HIGH-
SPEED TRANSISTOR

ATTY. REFERENCE: HWAN3013/EM

RECEIVED
 JUN -4 2003
 TECHNOLOGY CENTER 2800

COMMISSIONER OF PATENTS

P.O. Box 1450

Alexandria, VA 22313-1450

Sir:

Transmitted herewith is a communication/amendment in the above-identified application.

- ☐ Small entity status under 37 CFR 1.9 and 1.27 is claimed.
- ☒ No additional fee is required.

The fee, if any, has been calculated as shown below:

Fee Basis	Number of Claims After Amendment	Highest Number Previously Paid For	Extra Claims	Small Entity	Full Fee
Total Claims	20	- 20 ¹	= 0 ³	× \$ 9 =	× \$ 18 = \$0.00
Independent Claims	2	- 3 ²	= 0 ³	× \$ 42 =	× \$ 84 = \$0.00
<input type="checkbox"/> First Presentation of Proper Multiple Dependent Claim				+ \$140 =	+ \$280 =
TOTAL					\$0.00

¹ If less than 20 enter 20.

² If less than 3 enter 3.

³ If less than 0 enter 0.

- ☐ Please charge my Deposit Account Number 02-0200 in the amount of \$ _____. A duplicate copy of this sheet is attached.
- ☐ A check in the amount of \$ _____ is attached.
- ☒ The Commissioner is hereby authorized to charge any additional fees associated with this communication, including fees due under 37 CFR 1.16 and 37 CFR 1.17 or credit any overpayment to Deposit Account Number 02-0200. A duplicate copy of this sheet is attached.
- ☐ Also enclosed is/are:

BACON & THOMAS, PLLC
625 SLATERS LANE - FOURTH FLOOR
ALEXANDRIA, VIRGINIA 223124-1176
(703) 683-0500



23364

PATENT TRADEMARK OFFICE

Respectfully submitted,

Richard E. Fichter

Richard E. Fichter
Attorney for Applicant
Registration Number: 26,382

DATE: June 3, 2003



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Re Application of:

HWANG et al.

Group Art Unit: 2814

Serial No.: 10/022,349

Examiner: D. Wille

Filed: December 20, 2001

For: A SINGLE-CHIP STRUCTURE OF SILICON GERMANIUM
PHOTODETECTOR AND HIGH-SPEED TRANSISTOR

#7/C
marshu
6/6/03

TECHNOLOGY CENTER 2800

JUN-4 2003

RECEIVED

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

This is in response to the Official Action of March 3, 2003, in connection with the above-identified application.

Please amend the above-identified application as follows.

IN THE CLAIMS:

Please add the following new claims to the application.

37(New). A single-chip structure of silicon germanium photodetectors and high-speed transistors according to claim 20 wherein the insulation layer is perpendicular to and touches the substrate and goes through the base layer, photo-absorbing and collector layers.

38(New). A single-chip structure of silicon germanium photodetectors and high-speed transistors according to claim 29 wherein the insulation layer is perpendicular to and touches the substrate and goes through the base layer, photo-absorbing and collector layers.